

## METHOD OF INSPECTING HOLES USING CHARGED-PARTICLE BEAM

### ABSTRACT OF THE DISCLOSURE

This disclosure is directed to a method of inspecting how contact holes or via holes are formed in a sample, such as a wafer. An electron beam is directed to the contact holes in succession. An absorbed current flowing through the sample is detected by a current amplifier. Data about the obtained absorbed current is stored in a memory. The electric current flowing through a reference sample and ground is measured, and the relation of the current to the etch depths of contact holes into the substrate is previously found. A control unit compares data about the measured current with the previously found relation and determines the depths of holes of interest into the substrate (i.e., inspects how they are etched).